(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
20 August 2009 (20.08.2009)

PCT

(10) International Publication Number
WO 2009/102630 A1

(51) International Patent Classification:
B28D 5/00 (2006.01)

(21) International Application Number:
PCT/US2009/033363

(22) International Filing Date:
6 February 2009 (06.02.2009)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
61/027,512 11 February 2008 (11.02.2008) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR),

[Continued on next page]

(54) Title: CARBON NANOTUBE REINFORCED WIRESAW BEAM USED IN WIRESAW SLICING OF INGOTS INTO WAFERS

(57) Abstract: A wiresaw beam for use in an apparatus for slicing wafers from an ingot, such as semiconductor wafers from a single crystal ingot or a polycrystalline silicon ingot. The wiresaw beam may be made from a polymer composite material comprising a thermoset polymer resin and carbon nanotubes.

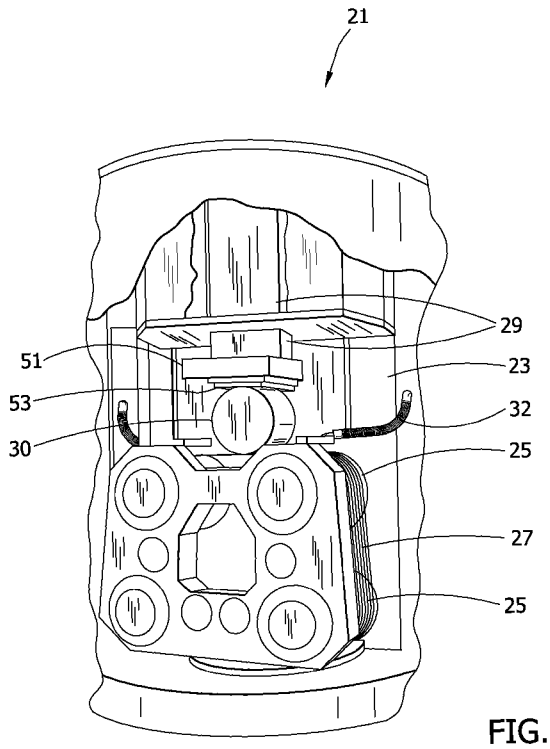


FIG. 1

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OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*